Bi-polar transistors

Power Transistor (120V, 7A)

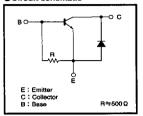
2SD1957

●Features

- 1) High DC current gain. (160~500)
- 2) Low VcE(sat). (Typ. 0.2V at lc/ls=3/0.3A)
- 3) Pc=30W. (Tc=25℃)
- 4) Wide SOA (safe operating area).
- 5) Built-in damper diode.

●Circuit schematic

Packaging specifications and hree Type 2SD1957 Package TO-220FP hre FG Code - Basic ordering unit (nieces) 500



●Absolute maximum ratings (Ta=25℃)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vceo	120	V	
Collector-emitter voltage	VCEO	120	V	
Emitter-base voltage	VEBO	5	٧	
Collector current		7	A (DC)	
	IC IC	lc 12		
Diode current	lo	7	A	
Collector power dissipation	_	2	w	
	Pc	30	W(Tc=25℃)	
Junction temperature	Tj	150	ర	
Storage temperature	Tstg	-55~150	r	

* Sigle pulse Pw=100ms

Electrical characteristics

(Ta=25℃)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	120	_		٧	Ic=50 μ A	
Collector-emitter breakdown voltage	BVcec	120			٧	Ic=1mA	
Emitter-base breakdown voltage	BVEBO	5			ν	I==30mA	
Collector cutoff current	Iceo	_	_	10	μA	Vcs=100V	
Emitter cutoff current	IEBO		· –	20	mA	V _{EB} =4V	
Collector-emitter saturation voltage	VCE(sat)		0.2	1	V	Ic/Is=3A/0.3A	*
Base-emitter saturation voltage	VBE(set)		0.9	1.5	V	Ic/Is=3A/0.3A	*
DC current transfer ratio	hre	160	-	500	_	VcE/Ic=5V/1A	
Transition frequency	fτ	_	40	_	MHz	Vce=5V , le=-0.5A , f=10MHz	*
Output capacitance	Cob	_	100	_	pF	Vcs=10V, le=0A, f=1MHz	
Diode forward current	VECF		_	3	V	lo=7A	*

^{*} Measured using pulse current.

(94L-919-D301)

Power Transistor (60V, 3A)

2SD2061

Features

- 1) Low VcE(sat). (Typ. 0.3V at Ic/Is=2/0.2A)
- 2) Excellent DC current gain characteristics.
- 3) Pc=30W. (Tc=25℃)
- 4) Wide SOA (safe operating area).

●Packaging specifications and her

2SD2061
TO-220FP
EF
_
500

●Absolute maximum ratings (Ta=25℃)

Parameter	Symbol	Limits	Unit			
Collector-base voltage	Vсво	80	V			
Collector-emitter voltage	Vceo	60	V			
Emitter-base voltage	VEBO	5	V			
Collector current		. 3 A(DC)				
	lc lc	6	A (Pulse) *			
Collector power dissipation		2 W				
	Pc	30	W (Tc=25℃)			
Junction temperature	Υj	150	°C			
Storage temperature	Tstg	~55~150	ວ			

* Sigle pulse Pw=100ms

●Electrical characteristics (Ta=25℃)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	80	_	_	٧	Ic=50 μ A	
Collector-emitter breakdown voltage	ВУсво	60			V	Ic=1mA	
Emitter-base breakdown voltage	ВУево	5		l –	٧	1ε=50 μ A	
Collector cutoff current	Ісво	_	_	10	μΑ	Vce=60V	
Emitter cutoff current	lebo	_	_	10	μΑ	VEB=4V	
Collector-emitter saturation voltage	VCE(sel)		_	1		Ic/Is=2A/0.2A	*
Base-emitter saturation voltage	VBE(sat)		-	1.5		Ic/le=2A/0.2A	*
DC current transfer ratio	hre	100	_	320		Vce/lc=5V/0.5A	-
Transition frequency	fτ		8	-		Vc=5V , I=-0.5A , f=5MHz	*
Output capacitance	Cob	T —	70	_	pF	Vcs=10V , IE=0A , f=1MHz	

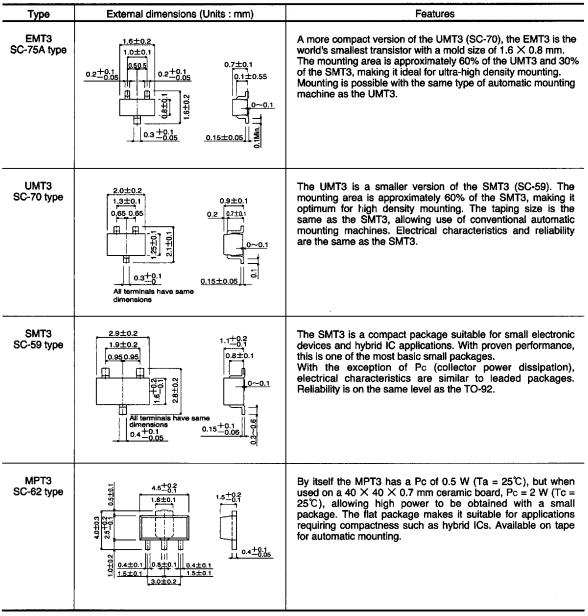
* Measured using pulse current.

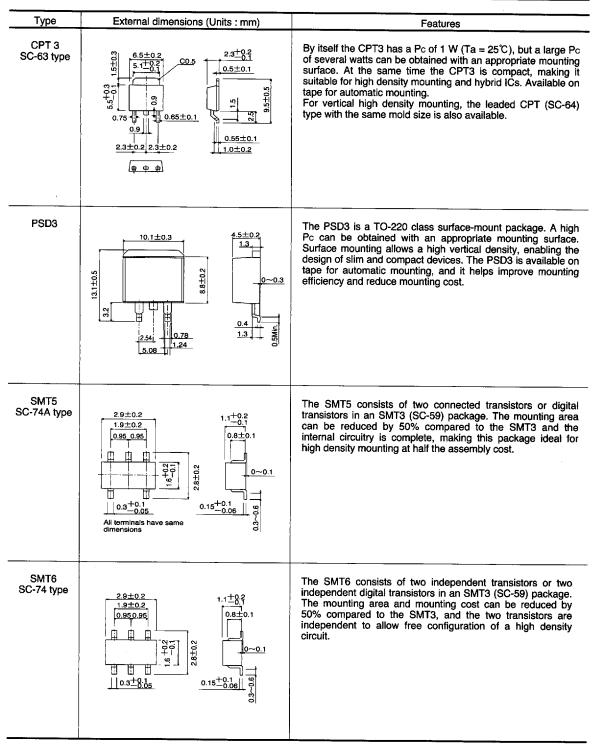
7828999 0016966 8T3 ■ (94L-1016-D304)

Packages

ROHM has been manufacturing transistors since 1975. In the development of products, we constantly strive to anticipate the needs of our customers. Regarding packages, the demands of the market for compactness, low power consumption, low power dissipation and automatic mounting support are becoming ever greater, and we are strengthening our product development system to meet these needs.

Types and features of surface-mount packages

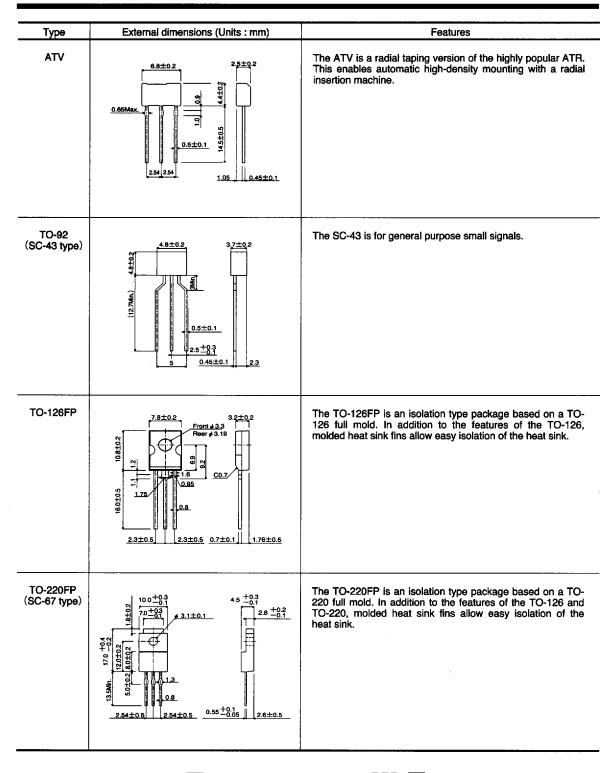




Туре	External dimensions (Units : mm)	Features
UMT5 SC-88A type	2.0±0.2 1,3±0.1 0,65 0,95 1,3±0.1 0,7 1,3±0.1 0,7 1,3±0.1 0,7 1,3±0.1 0,7 1,3±0.1 0,7 1,3±0.1 1,3±0.1 1,0,0,0,0,0,0 1,0,0,0,0,0 1,0,0,0,0,0 1,0,0,0,0,0 1,0,0,0,0,0 1,0,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0,0,0 1,0,0 1,0 1	The UMT5 consists of two connected transistors or digital transistors in a UMT3 (SC-70) package. The mounting area can be reduced by 50% compared to the UMT3 and the internal circuitry is completed, making this package ideal for high density mounting at half the assembly cost.
UMT6 SC-88 type	2.0±0.2 1.3±0.1 0.65 0.65 0.7 0.7 0.7 0.7 0.7 0.7 0.7 0.7	The UMT6 consists of two independent transistors or two independent digital transistors in a UMT (SC-70) package. The mounting area and mounting cost can be reduced by 50% compared to the UMT3, and the two transistors are independent to allow free configuration of a high density circuit.

●Types and features of leaded packages

Туре	External dimensions (Units : mm)	Features
SPT (SC-72 type)	2±0,2 0.45±0.15 0.45±0.15 0.5 0.45±0.15 0.5 0.45±0.15	The SPT is a smaller version of the conventional TO-92 type. The body size (3×4×2 mm³) has been reduced to 1/4 that of the TO-92 (5×5×4 mm³). The SPT is available on tape for automatic insertion, and less space is occupied on the printed circuit board than the TO-92. Reliability is the same as the TO-92.
FTR	0.65±0.1 2.4±0.2 0.55±0.1 0.55±0.1 0.45±0.1 0.45±0.1	SIL type with a height of 3.4 mm and a lead pitch of 2.54 mm.
FTL	0.65Max 2.4±0.2 0.65Max 2.4±0.2 0.5±0.1 0.5±0.1	The FTL is a radial taping version of the highly popular FTR. This enables automatic high-density mounting with a radial insertion machine.
ATR (SC-71 type)	0.65Max	SC-71type with a height of 4.4 mm and a Pc=1W type.



Type	External dimensions (Units : mm)	Features
TO-220FN	\$3.2±0.2	The TO-220FN features the same performance as the TO-220FP with approximately 2 mm less height, allowing the design of slimmer devices. Furthermore, the elimination of support pins in the fin (collector electrode) solves short-circuiting problems with neighboring components and the chassis. To make the height to the installation hole the same as the TO-220FP, it can be replaced as is from the TO-220FP.